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a second insulating film comprising an organic resin formed over said first inorganic insulating film;
an electrode formed over said second insulating film and connected to one of said first and second impurity regions; and
a pixel electrode formed over said second insulating film.

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3. (Amended) A semiconductor device of claim 1 wherein said first inorganic insulating film comprises silicon oxide.

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8. (Amended) A semiconductor device comprising:
a semiconductor layer having at least first and second impurity regions and a channel region formed on an insulating surface;
a gate insulating film formed on said semiconductor layer;
a gate electrode formed on said gate insulating film;
a first inorganic insulating film covering at least said gate electrode and said semiconductor layer except for contact holes opened therein;
a second insulating film comprising an organic resin formed over said first inorganic insulating film;
an electrode formed over said second insulating film and connected to one of said first and second impurity regions; and
a pixel electrode formed over said second insulating film.

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10. (Amended) A semiconductor device of claim 8 wherein said first inorganic insulating film comprises silicon oxide.

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15. (Amended) A semiconductor device comprising:
a semiconductor layer having at least first and second impurity regions and a channel region formed on an insulating surface;
a gate insulating film adjacent to said semiconductor layer;
a gate electrode adjacent to said gate insulating film;
a first inorganic insulating film covering at least said gate electrode and said semiconductor layer except for contact holes opened therein;

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a second insulating film comprising an organic resin formed over said first inorganic insulating film;
an electrode formed over said second insulating film and connected to one of said first and second impurity regions; and
a transparent pixel electrode formed over said second insulating film.

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17. (Amended) A semiconductor device of claim 15 wherein said first inorganic insulating film comprises silicon oxide.

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23. (Amended) A semiconductor device comprising:
a semiconductor layer having at least first and second impurity regions and a channel region formed on an insulating surface;
a gate insulating film formed on said semiconductor layer;
a gate electrode formed on said gate insulating film;
a first inorganic insulating film covering at least said gate electrode and said semiconductor layer except for contact holes opened therein;
a second insulating film comprising an organic resin formed over said first inorganic insulating film;
an electrode formed over said second insulating film and connected to one of said first and second impurity regions; and
a transparent pixel electrode formed over said second insulating film.

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25. (Amended) A semiconductor device of claim 23 wherein said first inorganic insulating film comprises silicon oxide.

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31. (Amended) A semiconductor device comprising:
a semiconductor layer having at least first and second impurity regions and a channel region formed on an insulating surface;
a gate insulating film adjacent to said semiconductor layer;
a gate electrode adjacent to said gate insulating film;
a first inorganic insulating film covering at least said gate electrode and said semiconductor layer except for contact holes opened therein;

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a second insulating film comprising an organic resin formed over said first inorganic insulating film;

an electrode formed over said second insulating film and connected to one of said first and second impurity regions, wherein said electrode has a laminate structure including a first conductive film comprising aluminum and a second conductive film comprising a different material from said first conductive film;

a pixel electrode formed over said second insulating film and electrically connected to said one of said first and second impurity regions through said electrode; and

a conductive layer formed over said second insulating film and connected to the other one of said first and second impurity regions.

33. (Amended) A semiconductor device of claim 31 wherein said first inorganic insulating film comprises silicon oxide.

36. (Amended) A semiconductor device comprising:

a semiconductor layer having at least first and second impurity regions and a channel region formed on an insulating surface;

a gate insulating film adjacent to said semiconductor layer;

a gate electrode adjacent to said gate insulating film;

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a first inorganic insulating film covering at least said gate electrode and said semiconductor layer except for contact holes opened therein;

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a second insulating film comprising an organic resin formed over said first inorganic insulating film;

an electrode formed over said second insulating film and connected to one of said first and second impurity regions, wherein said electrode has a laminate structure including a first conductive film comprising aluminum and a second conductive film comprising a different material from said first conductive film;

a transparent pixel electrode formed over said second insulating film and electrically connected to said one of said first and second impurity regions through said electrode; and

a conductive layer formed over said second insulating film and connected to the other one of said first and second impurity regions.

~~CP~~ 1 38. (Amended) A semiconductor device of claim 36 wherein said first inorganic insulating film comprises silicon oxide.

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~~CP~~ 3 42. (Amended) A semiconductor device comprising:
a semiconductor layer having at least first and second impurity regions and a channel region formed on an insulating surface;
a gate insulating film adjacent to said semiconductor layer;
a gate electrode adjacent to said gate insulating film;
a first inorganic insulating film covering at least said gate electrode and said semiconductor layer except for contact holes opened therein;
a second insulating film comprising an organic resin formed over said first inorganic insulating film;
an electrode formed over said second insulating film and connected to one of said first and second impurity regions, wherein said electrode has a laminate structure including a first conductive film comprising aluminum and a second conductive film comprising a different material from said first conductive film;
a transparent pixel electrode formed over said second insulating film and electrically connected to said one of said first and second impurity regions through said electrode; and
a conductive layer formed over said second insulating film and connected to the other one of said first and second impurity regions, wherein said electrode comprises a same material as said conductive layer.

~~CP~~ 4 D1 44. (Amended) A semiconductor device of claim 42 wherein said first inorganic insulating film comprises silicon oxide.

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~~CP~~ 5 48. (Amended) A semiconductor device comprising:
a semiconductor layer having at least first and second impurity regions and a channel region formed on an insulating surface;
a gate insulating film adjacent to said semiconductor layer;
a gate electrode adjacent to said gate insulating film;

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a first inorganic insulating film covering at least said gate electrode and said semiconductor layer except for contact holes opened therein;

a second insulating film comprising an organic resin formed over said first inorganic insulating film;

an electrode formed over said second insulating film and connected to one of said first and second impurity regions;

a pixel electrode formed over said second insulating film and electrically connected to said one of said first and second impurity regions through said electrode; and

a conductive layer formed over said second insulating film and connected to the other one of said first and second impurity regions,

wherein a portion of said pixel electrode is located below said electrode.

50. (Amended) A semiconductor device of claim 48 wherein said first inorganic insulating film comprises silicon oxide.